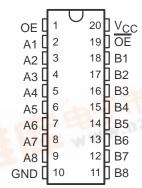
2.5-V/3.3-V LOW-VOLTAGE HIGH-BANDWIDTH BUS SWITCH

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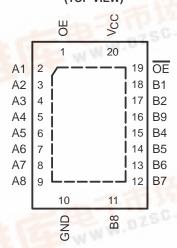
- High-Bandwidth Data Path
 (Up To 500 MHz[†])
- 5-V Tolerant I/Os with Device Powered-Up or Powered-Down
- Low and Flat ON-State Resistance (r_{on})
 Characteristics Over Operating Range (r_{on} = 4 Ω Typical)
- Rail-to-Rail Switching on Data I/O Ports
 0- to 5-V Switching With 3.3-V V_{CC}
 0- to 3.3-V Switching With 2.5-V V_{CC}
- Bidirectional Data Flow, With Near-Zero Propagation Delay
- Low Input/Output Capacitance Minimizes Loading and Signal Distortion (Cio(OFF) = 4 pF Typical)
- Fast Switching Frequency (f_{OE} = 20 MHz Max)
 - † For additional information regarding the performance characteristics of the CB3Q family, refer to the TI application report, *CBT-C, CB3T, and CB3Q Signal-Switch Families*, literature number SCDA008.

- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption (I_{CC} = 0.7 mA Typical)
- V_{CC} Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0 to 5-V Signaling Levels
 (0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)
- Control Inputs Can be Driven by TTL or 5-V/3.3-V CMOS Outputs
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 2000-V Human-Body Model
 (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: Differential Signal Interface, Memory Interleaving, Bus Isolation, Low-Distortion Signal Gating

DBQ, DGV, OR PW PACKAGE (TOP VIEW)



RGY PACKAGE (TOP VIEW)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

2.5-V/3.3-V LOW-VOLTAGE HIGH-BANDWIDTH BUS SWITCH

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description/ordering information

The SN74CB3Q3345 is a high-bandwidth FET bus switch utilizing a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance (r_{on}). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q3345 provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.

The SN74CB3Q3384A is organized as an 8-bit bus switch with two output-enable (\overline{OE}) inputs. When OE is high or \overline{OE} is low, the bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is low and \overline{OE} is high, the bus switch is OFF, and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry prevents damaging current backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

ORDERING INFORMATION

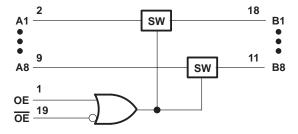
TA	PACKAGE [†]		ORDERABLE PART NUMBER	TOP-SIDE MARKING
	QFN – RGY	Tape and reel	SN74CB3Q3345RGYR	BU345
	SSOP (QSOP) – DBQ	Tape and reel	SN74CB3Q3345DBQR	CB3Q3345
-40°C to 85°C	TCCOD DW	Tube	SN74CB3Q3345PW	DI IO45
	TSSOP – PW	Tape and reel	SN74CB3Q3345PWR	BU345
	TVSOP - DGV	Tape and reel	SN74CB3Q3345DGVR	BU345

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE

INP	UTS	INPUT/OUTPUT	FUNCTION
OE	OE	Α	FUNCTION
Н	Х	В	A port = B port
Х	L	В	A port = B port
L	Н	Z	Disconnect

logic diagram (positive logic)

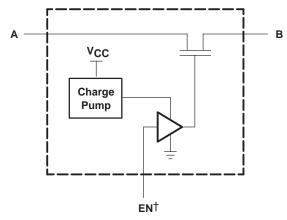




2.5-V/3.3-V LOW-VOLTAGE HIGH-BANDWIDTH BUS SWITCH

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simplified schematic, each FET switch (SW)



[†]EN is the internal enable signal applied to the switch.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC} –	0.5 V to 4.6 V
Control input voltage range, V _{IN} (see Notes 1 and 2)	-0.5 V to 7 V
Switch I/O voltage range, V _{I/O} (see Notes 1, 2, and 3)	-0.5 V to 7 V
Control input clamp current, I _{IK} (V _{IN} < 0)	–50 mA
I/O port clamp current, $I_{I/OK}$ ($V_{I/O}$ < 0)	–50 mA
ON-state switch current, I _{I/O} (see Note 4)	±64 mA
Continuous current through V _{CC} or GND terminals	±100 mA
Package thermal impedance, θ_{JA} (see Note 5): DBQ package	68°C/W
(see Note 5): DGV package	92°C/W
(see Note 5): PW package	83°C/W
(see Note 6): RGY package	37°C/W
Storage temperature range, T _{stq} 6	35°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
 - 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 3. V_I and V_O are used to denote specific conditions for V_{I/O}.
 - 4. If and IO are used to denote specific conditions for II/O.
 - 5. The package thermal impedance is calculated in accordance with JESD 51-7.
 - 6. The package thermal impedance is calculated in accordance with JESD 51-5.

recommended operating conditions (see Note 7)

		MIN	MAX	UNIT
Vcc	Supply voltage	2.3	3.6	V
.,	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		5.5	.,
VIH	High-level control input voltage $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2	5.5	V
.,	Low-level control input voltage $ \frac{V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}}{V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}} $		0.7	.,
VIL			0.8	V
V _{I/O}	Data input/output voltage	0	5.5	V
T _A Operating free-air temperature		-40	85	°C

NOTE 7: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



SN74CB3Q3345 **8-BIT FET BUS SWITCH**

2.5-V/3.3-V LOW-VOLTAGE HIGH-BANDWIDTH BUS SWITCH

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAI	RAMETER	TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT	
VIK		$V_{CC} = 3.6 \text{ V},$	$I_{I} = -18 \text{ mA}$				-1.8	V
I _{IN}	Control inputs	$V_{CC} = 3.6 \text{ V},$	$V_{IN} = 0 \text{ to } 5.5 \text{ V}$				±1	μΑ
loz‡		V _{CC} = 3.6 V,	$V_O = 0 \text{ to } 5.5 \text{ V},$ $V_I = 0,$	Switch OFF, V _{IN} = V _{CC} or GND			±1	μА
l _{off}		$V_{CC} = 0$,	$V_0 = 0 \text{ to } 5.5 \text{ V},$	V _I = 0			1	μΑ
Icc		V _{CC} = 3.6 V,	$I_{I/O} = 0$, Switch ON or OFF,	V _{IN} = V _{CC} or GND		0.7	2	mA
Δl _{CC} §	Control inputs	$V_{CC} = 3.6 \text{ V},$	One input at 3 V,	Other inputs at V _{CC} or GND			30	μΑ
ICCD¶	Per control input	V _{CC} = 3.6 V, Control input switching	A and B ports open, at 50% duty cycle			0.13	0.14	mA/ MHz
C _{in}	Control inputs	$V_{CC} = 3.3 \text{ V},$	V _{IN} = 5.5 V, 3.3 V, or 0			2.5	3.5	pF
C _{io(OFF}	=)	V _{CC} = 3.3 V,	Switch OFF, $V_{IN} = V_{CC}$ or GND,	V _{I/O} = 5.5 V, 3.3 V, or 0		3.5	5	pF
C _{io(ON)})	V _{CC} = 3.3 V,	Switch ON, $V_{IN} = V_{CC}$ or GND,	V _{I/O} = 5.5 V, 3.3 V, or 0		9	11.5	pF
		$V_{CC} = 2.3 V$,	V _I = 0,	$I_O = 30 \text{ mA}$		4	8	
r _{on} #	_ #	TYP at $V_{CC} = 2.5 \text{ V}$	V _I = 1.7 V,	I _O = -15 mA		4.5	9	Ω
'on"		V _I = 0,	V _I = 0,	I _O = 30 mA		4	6	52
		VCC = 3 V	V _I = 2.4 V,	$I_O = -15 \text{ mA}$		4.5	8	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM	TO	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	
fOE or fOE	OE or OE	A or B		10		20	MHz
t _{pd} ☆	A or B	B or A		0.12		0.2	ns
t _{en}	OE or OE	A or B	1.5	7.7	1.5	6.5	ns
^t dis	OE or OE	A or B	1	6.9	1	6.8	ns

Maximum switching frequency for control input $(V_O > V_{CC}, V_I = 5 \text{ V}, R_I \ge 1 \text{ M}\Omega, C_I = 0)$



 V_{IN} and I_{IN} refer to control inputs. V_I , V_O , I_I , and I_O refer to data pins. † All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.

For I/O ports, the parameter IOZ includes the input leakage current.

[§] This is the increase in supply current for each input that is at the specified TTL voltage level, rather than VCC or GND.

[¶]This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see Figure 2).

[#] Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

^{*}The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

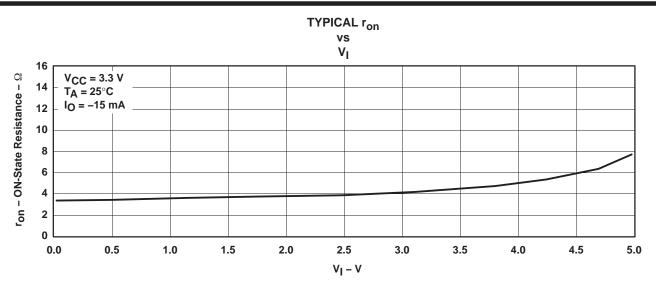


Figure 1. Typical r_{on} vs V_{I} , V_{CC} = 3.3 V and I_{O} = -15 mA

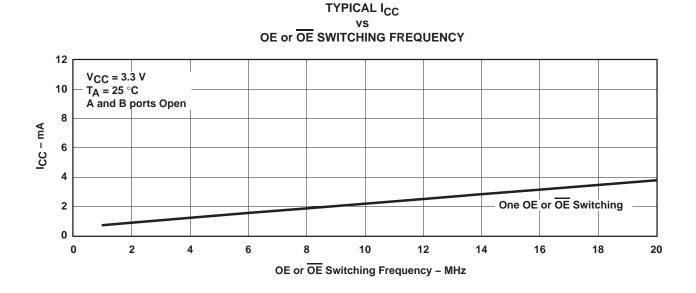
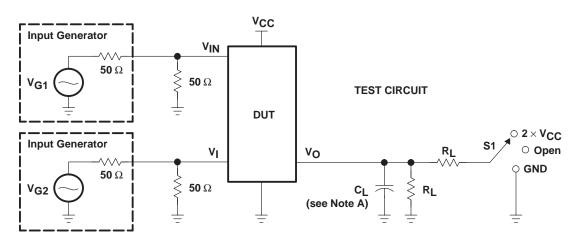


Figure 2. Typical I_{CC} vs OE or \overline{OE} Switching Frequency, V_{CC} = 3.3 V

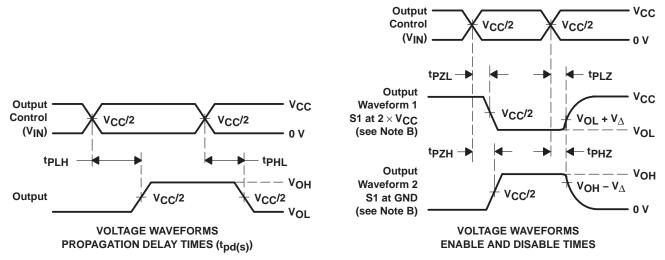


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PARAMETER MEASUREMENT INFORMATION



TEST	V _{CC}	S1	RL	VI	CL	$v_{\!\scriptscriptstyle\Delta}$
^t pd(s)	$\begin{array}{c} \textbf{2.5 V} \pm \textbf{0.2 V} \\ \textbf{3.3 V} \pm \textbf{0.3 V} \end{array}$	Open Open	500 Ω 500 Ω	V _{CC} or GND V _{CC} or GND	30 pF 50 pF	
tPLZ/tPZL	$\begin{array}{c} \textbf{2.5 V} \pm \textbf{0.2 V} \\ \textbf{3.3 V} \pm \textbf{0.3 V} \end{array}$	2×V _{CC} 2×V _{CC}	500 Ω 500 Ω	GND GND	30 pF 50 pF	0.15 V 0.3 V
tPHZ/tPZH	$\begin{array}{c} \textbf{2.5 V} \pm \textbf{0.2 V} \\ \textbf{3.3 V} \pm \textbf{0.3 V} \end{array}$	GND GND	500 Ω 500 Ω	v _{CC}	30 pF 50 pF	0.15 V 0.3 V



NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50~\Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd(s). The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.

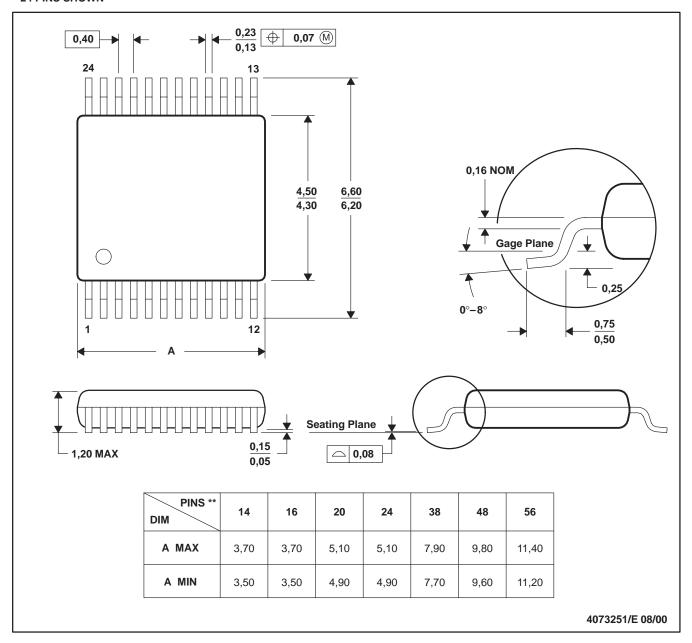
Figure 3. Test Circuit and Voltage Waveforms



DGV (R-PDSO-G**)

24 PINS SHOWN

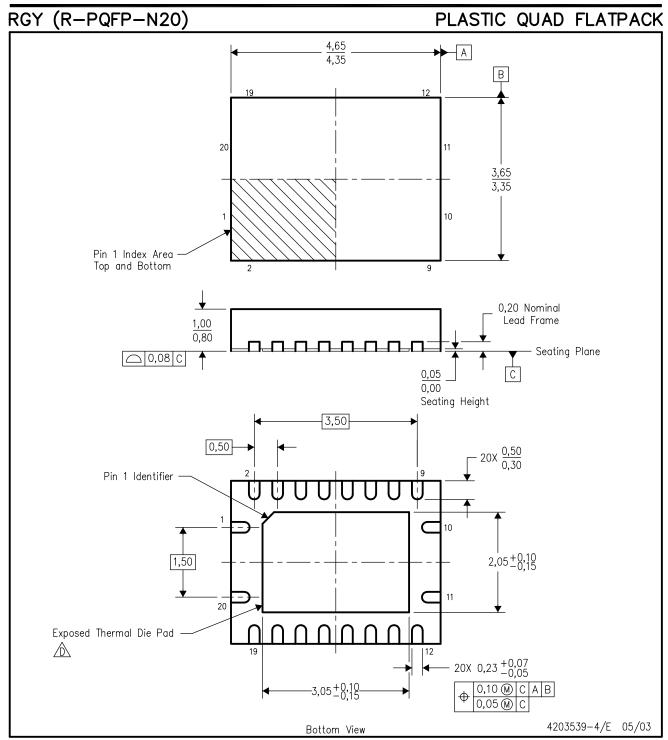
PLASTIC SMALL-OUTLINE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
- D. Falls within JEDEC: 24/48 Pins MO-153 14/16/20/56 Pins – MO-194





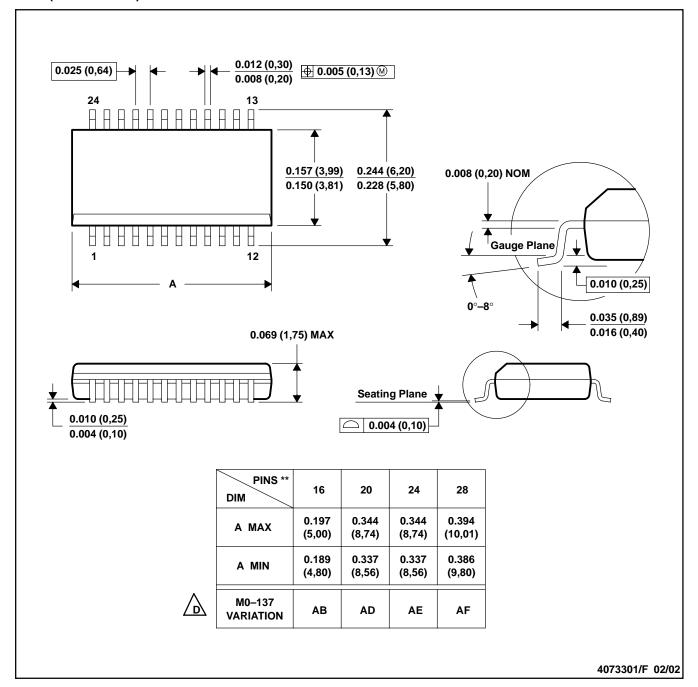
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- The package thermal performance may be enhanced by bonding the thermal die pad to an external thermal plane. This pad is electrically and thermally connected to the backside of the die and possibly selected ground leads.
- E. Package complies to JEDEC MO-241 variation BC.



DBQ (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

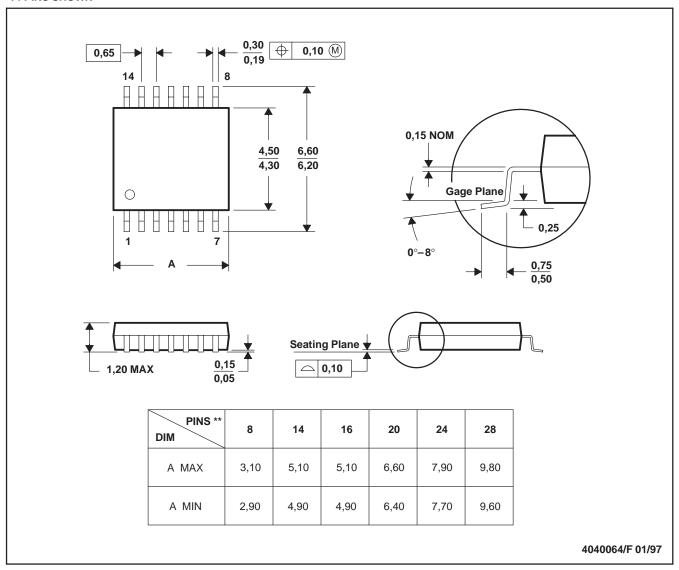
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MO-137.



PW (R-PDSO-G**)

14 PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153

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